

Switching diode

1SS400G

●Applications

High frequency switching

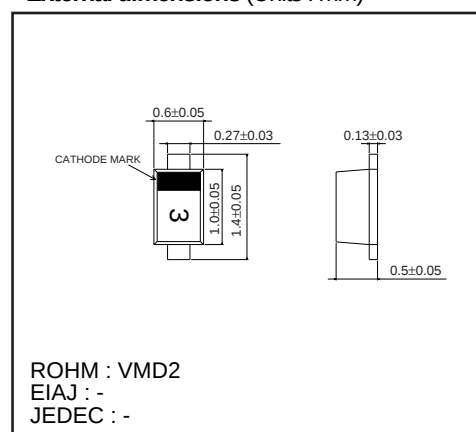
●Features

- 1) Ultra small mold type. (VMD2)
- 2) High reliability.

●Construction

Silicon epitaxial planar

●External dimensions (Units : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	90	V
DC reverse voltage	V_R	80	V
Peak forward current	I_{FM}	225	mA
Mean rectifying current	I_o	100	mA
Surge current (1s)	I_{surge}	500	mA
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55~+150	°C

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	—	1.2	V	$I_F=100\text{mA}$
Reverse current	I_R	—	—	100	nA	$V_R=80\text{V}$
Capacitance between terminals	C_T	—	—	3.0	pF	$V_R=0.5\text{V}$, $f=1\text{MHz}$
Reverse recovery time	t_{rr}	—	—	4.0	ns	$V_R=6\text{V}$, $I_F=10\text{mA}$, $R_L=100\Omega$

Diodes

●Electrical characteristic curves (Ta=25°C)

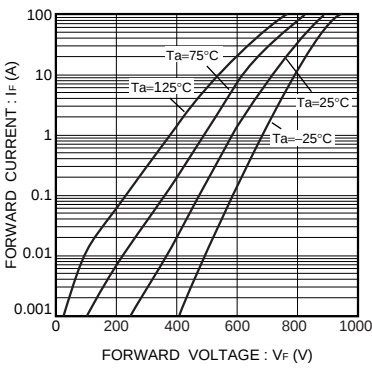


Fig.1 Forward characteristics

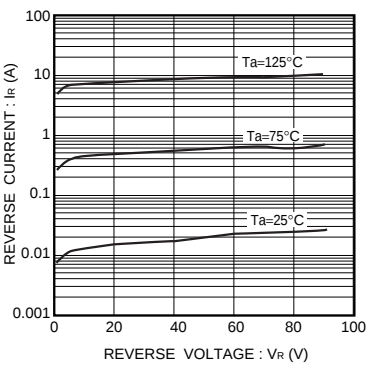


Fig.2 Reverse characteristics

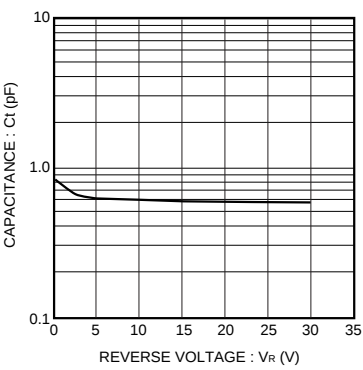


Fig.3 Characteristics